

## TRANSISTOR (NPN)

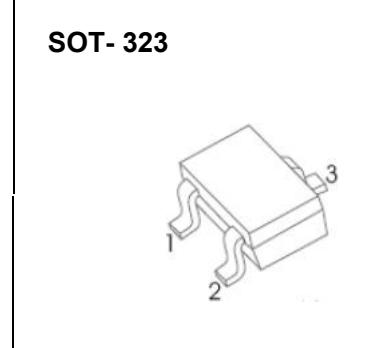
### FEATURE

High DC current gain : $h_{FE}=200$ (Typ) $V_{CE}=6V$ ,  $I_c=1mA$

High voltage:  $V_{CEO}=50V$

**MAXIMUM RATINGS** ( $T_A=25^\circ C$  unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_c$	Collector Current -Continuous	100	mA
$P_c$	Collector Power Dissipation	200	mW
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55-150	°C



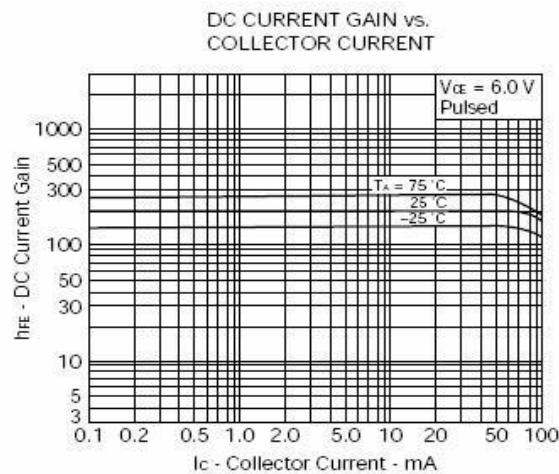
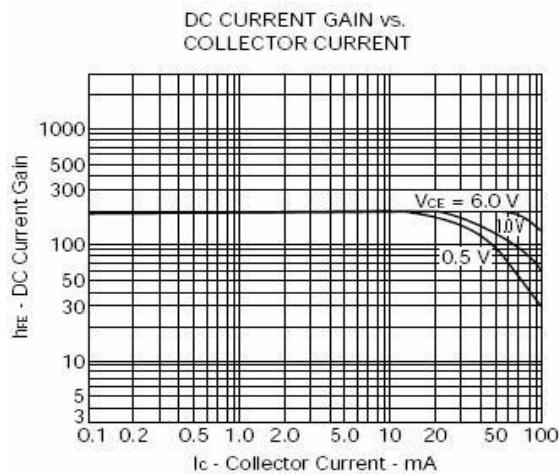
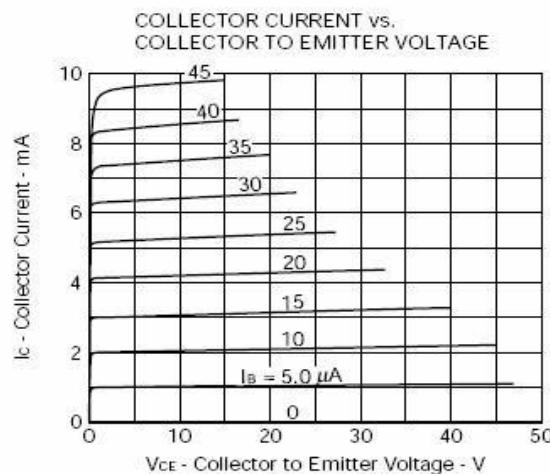
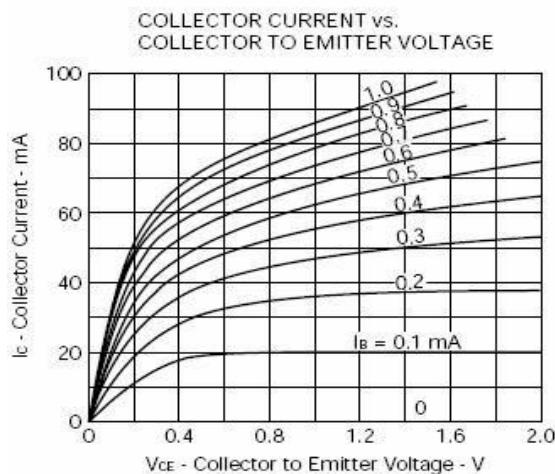
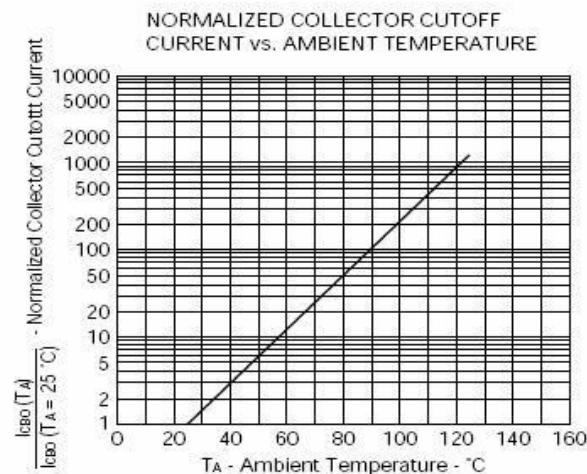
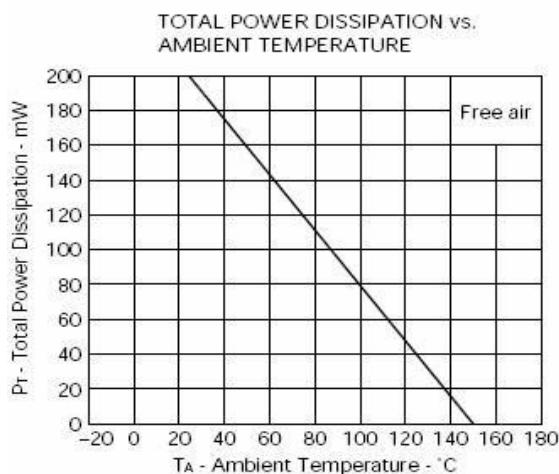
### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=6V, I_c=1mA$	90		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	$f_T$	$V_{CE}=6V, I_c=10mA$		250		MHz

### CLASSIFICATION OF hFE

Range	90-180	135-270	200-400	400-700
Marking	L4	L5	L6	L7

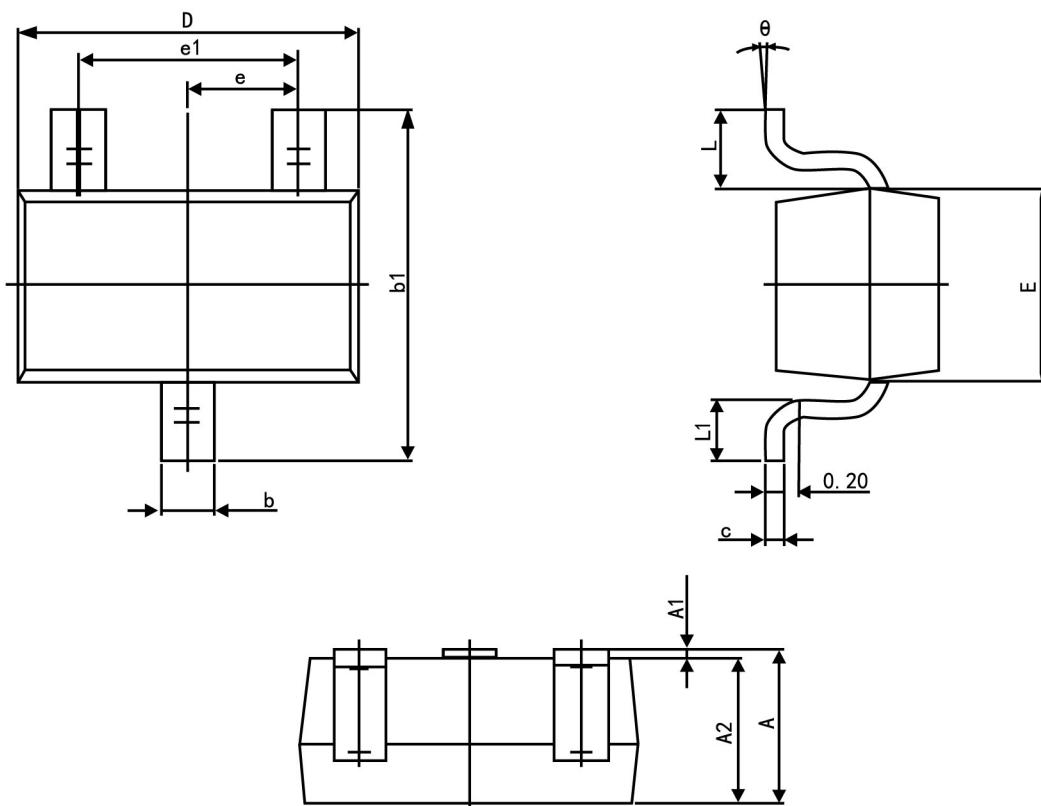
## Typical Characteristics



## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

**SOT-323**



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	0°	8°